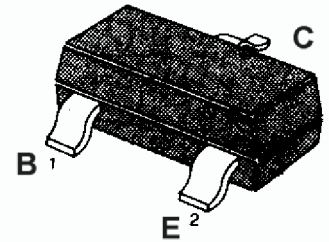


APPLICATION: High Frequency Amplifier Applications.
FM, RF, MIX,IF Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _C	20	mA
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	40		200		V _{CE} = 6 V, I _C = 1mA
Collector Cut-off Current	I _{CBO}			0.5	μA	V _{CB} = 18 V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.5	μA	V _{EB} = 4 V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	40			V	I _C = 0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	30			V	I _C = 1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	4			V	I _E = 0.1 mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.4	V	I _C = 10 mA, I _B = 1 mA
Gain bandwidth product	f _T	400	550		MHz	I _C = 1 mA, V _{CE} = 6 V
Common Base Output Capacitance	C _{re}		0.7	2	pF	V _{CB} = 6 V, f = 1 MHz
Power Gain	G _P	15	18		dB	V _{CE} = 6 V, I _E = 1 mA
Noise Figure	N _F		2.5	5	dB	V _{CE} = 6 V, I _C = 1mA, f =100 MHz

h_{FE} Classification And Marking

Print Mark	QR	QO	QY
Classification	R	O	Y
h _{FE}	40~80	70~140	100~200